

# NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL

## Ignition IGBT 15 A, 410 V N-Channel DPAK, D<sup>2</sup>PAK and TO-220

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Over-Voltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

### Features

- Ideal for Coil-on-Plug Applications
- DPAK Package Offers Smaller Footprint and Increased Board Space
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- New Design Increases Unclamped Inductive Switching (UIS) Energy Per Area
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- Optional Gate Resistor ( $R_G$ ) and Gate-Emitter Resistor ( $R_{GE}$ )
- These are Pb-Free Devices

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	440	$V_{DC}$
Collector-Gate Voltage	$V_{CER}$	440	$V_{DC}$
Gate-Emitter Voltage	$V_{GE}$	15	$V_{DC}$
Collector Current-Continuous @ $T_C = 25^\circ\text{C}$ - Pulsed	$I_C$	15 50	$A_{DC}$ $A_{AC}$
ESD (Human Body Model) $R = 1500 \Omega$ , $C = 100 \text{ pF}$	ESD	8.0	kV
ESD (Machine Model) $R = 0 \Omega$ , $C = 200 \text{ pF}$	ESD	800	V
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	107 0.71	Watts $\text{W}/^\circ\text{C}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



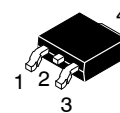
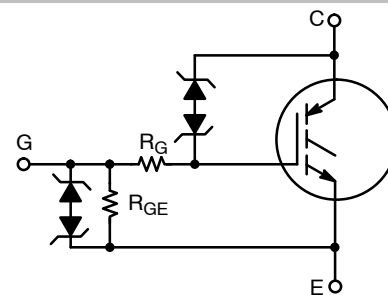
ON Semiconductor®

<http://onsemi.com>

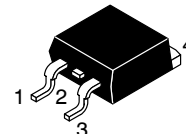
15 AMPS

410 VOLTS

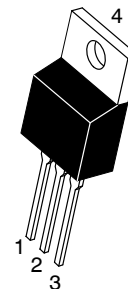
$V_{CE(on)} \leq 2.1 \text{ V @}$   
 $I_C = 10 \text{ A}, V_{GE} \geq 4.5 \text{ V}$



DPAK  
CASE 369C  
STYLE 2



D<sup>2</sup>PAK  
CASE 418B  
STYLE 4



TO-220AB  
CASE 221A  
STYLE 9

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

### DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 8 of this data sheet.

# NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL

## UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS ( $-55^{\circ} \leq T_J \leq 175^{\circ}C$ )

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , Pk $I_L = 16.6\text{ A}$ , $L = 1.8\text{ mH}$ , Starting $T_J = 25^{\circ}C$ $V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , Pk $I_L = 15\text{ A}$ , $L = 1.8\text{ mH}$ , Starting $T_J = 125^{\circ}C$	$E_{AS}$	250 200	mJ

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	$^{\circ}C/W$
Thermal Resistance, Junction to Ambient	DPAK (Note 1) $R_{\theta JA}$	100	
	D <sup>2</sup> PAK (Note 1) $R_{\theta JA}$	50	
	TO-220 $R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	$T_L$	275	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	$BV_{CES}$	$I_C = 2.0\text{ mA}$	$T_J = -40^{\circ}C$ to $150^{\circ}C$	380	410	440	$V_{DC}$
		$I_C = 10\text{ mA}$	$T_J = -40^{\circ}C$ to $150^{\circ}C$	380	410	440	
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE} = 350\text{ V}$ , $V_{GE} = 0\text{ V}$	$T_J = 25^{\circ}C$	-	2.0	20	$\mu A_{DC}$
			$T_J = 150^{\circ}C$	-	10	40*	
			$T_J = -40^{\circ}C$	-	1.0	10	
Reverse Collector-Emitter Leakage Current	$I_{ECS}$	$V_{CE} = -24\text{ V}$	$T_J = 25^{\circ}C$	-	0.7	2.0	mA
			$T_J = 150^{\circ}C$	-	12	25*	
			$T_J = -40^{\circ}C$	-	0.1	1.0	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75\text{ mA}$	$T_J = 25^{\circ}C$	27	33	37	$V_{DC}$
			$T_J = 150^{\circ}C$	30	36	40	
			$T_J = -40^{\circ}C$	25	31	35	
Gate-Emitter Clamp Voltage	$BV_{GES}$	$I_G = 5.0\text{ mA}$	$T_J = -40^{\circ}C$ to $150^{\circ}C$	11	13	15	$V_{DC}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{GE} = 10\text{ V}$	$T_J = -40^{\circ}C$ to $150^{\circ}C$	384	640	1000	$\mu A_{DC}$
Gate Resistor	$R_G$	-	$T_J = -40^{\circ}C$ to $150^{\circ}C$	-	70	-	$\Omega$
Gate Emitter Resistor	$R_{GE}$	-	$T_J = -40^{\circ}C$ to $150^{\circ}C$	10	16	26	k $\Omega$

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0\text{ mA}$ , $V_{GE} = V_{CE}$	$T_J = 25^{\circ}C$	1.1	1.4	1.9	$V_{DC}$
			$T_J = 150^{\circ}C$	0.75	1.0	1.4	
			$T_J = -40^{\circ}C$	1.2	1.6	2.1*	
Threshold Temperature Coefficient (Negative)	-	-	-	-	3.4	-	mV/ $^{\circ}C$

1. When surface mounted to an FR4 board using the minimum recommended pad size.

2. Pulse Test: Pulse Width  $\leq 300\ \mu s$ , Duty Cycle  $\leq 2\%$ .

\*Maximum Value of Characteristic across Temperature Range.

**NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL,  
NGP15N41ACL**

**ELECTRICAL CHARACTERISTICS (continued)**

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS (continued) (Note 3)</b>							
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.0 \text{ A},$ $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.6	1.8	$V_{DC}$
			$T_J = 150^\circ\text{C}$	0.9	1.5	1.8	
			$T_J = -40^\circ\text{C}$	1.1	1.65	1.9*	
		$I_C = 8.0 \text{ A},$ $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.3	1.8	2.0*	
			$T_J = 150^\circ\text{C}$	1.2	1.7	1.9	
			$T_J = -40^\circ\text{C}$	1.4	1.8	2.0*	
		$I_C = 10 \text{ A},$ $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.4	2.0	2.2	
			$T_J = 150^\circ\text{C}$	1.5	2.0	2.3*	
			$T_J = -40^\circ\text{C}$	1.4	2.0	2.2	
		$I_C = 10 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.3	1.9	2.1	
			$T_J = 150^\circ\text{C}$	1.3	1.9	2.1	
			$T_J = -40^\circ\text{C}$	1.4	1.95	2.1*	
Forward Transconductance	gfs	$V_{CE} = 5.0 \text{ V}, I_C = 6.0 \text{ A}$	$T_J = -40^\circ\text{C}$ to $150^\circ\text{C}$	8.0	15	25	Mhos

**DYNAMIC CHARACTERISTICS**

Input Capacitance	$C_{ISS}$	$V_{CC} = 25 \text{ V}, V_{GE} = 0 \text{ V}$ $f = 1.0 \text{ MHz}$	$T_J = -40^\circ\text{C}$ to $150^\circ\text{C}$	400	650	1000	pF
Output Capacitance	$C_{OSS}$			30	55	100	
Transfer Capacitance	$C_{RSS}$			3.0	4.5	8.0	

**SWITCHING CHARACTERISTICS**

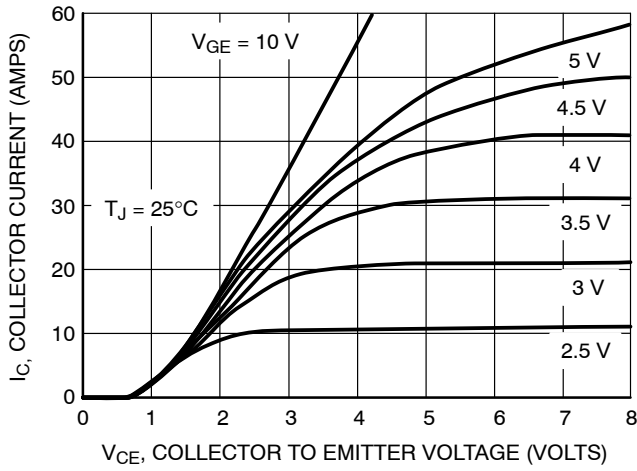
Turn-Off Delay Time (Inductive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, L = 300 \mu\text{H}$	$T_J = 25^\circ\text{C}$	-	4.0	10	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	4.5	10	
Fall Time (Inductive)	$t_f$	$V_{CC} = 300 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, L = 300 \mu\text{H}$	$T_J = 25^\circ\text{C}$	-	6.0	12	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	10	12	
Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, R_L = 46 \Omega,$	$T_J = 25^\circ\text{C}$	-	3.0	10	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	3.5	10	
Fall Time (Resistive)	$t_f$	$V_{CC} = 300 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, R_L = 46 \Omega,$	$T_J = 25^\circ\text{C}$	-	8.0	15	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	12	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 10 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, R_L = 1.5 \Omega$	$T_J = 25^\circ\text{C}$	-	0.7	4.0	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	0.7	4.0	
Rise Time	$t_r$	$V_{CC} = 10 \text{ V}, I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega, R_L = 1.5 \Omega$	$T_J = 25^\circ\text{C}$	-	4.0	7.0	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	5.0	7.0	

3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

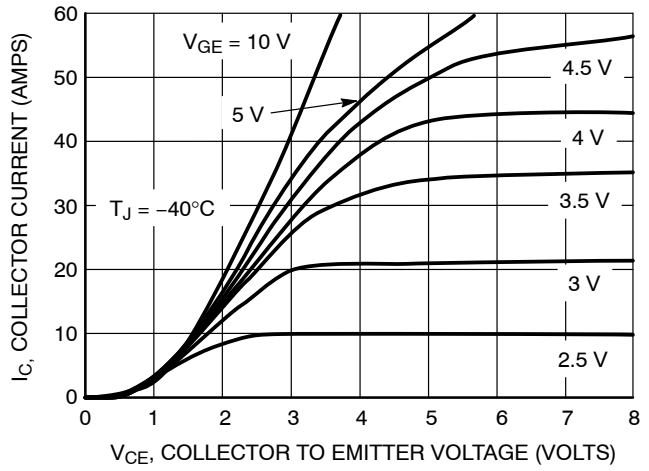
\*Maximum Value of Characteristic across Temperature Range.

**NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL**

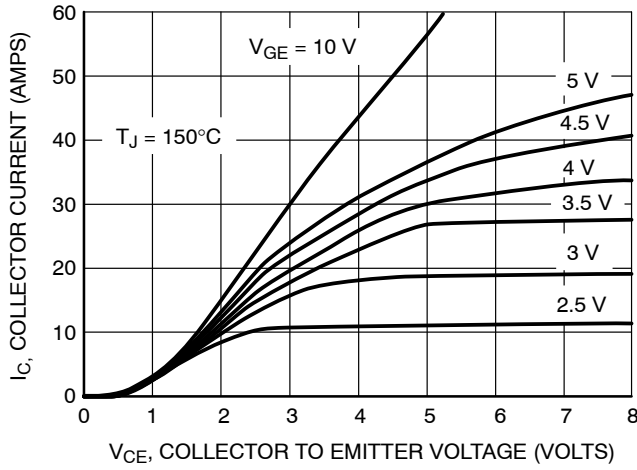
**TYPICAL ELECTRICAL CHARACTERISTICS (unless otherwise noted)**



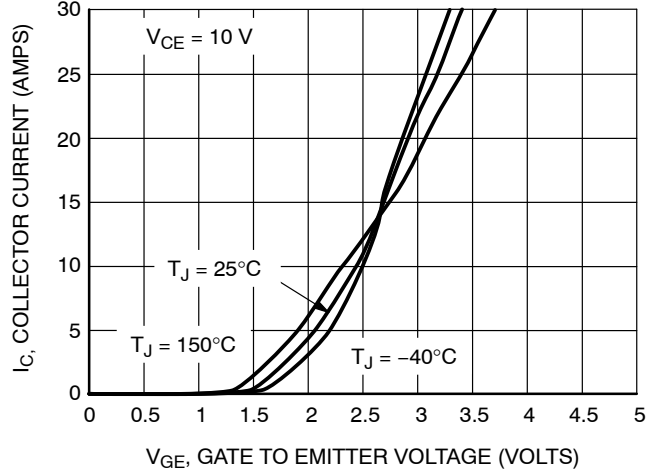
**Figure 1. Output Characteristics**



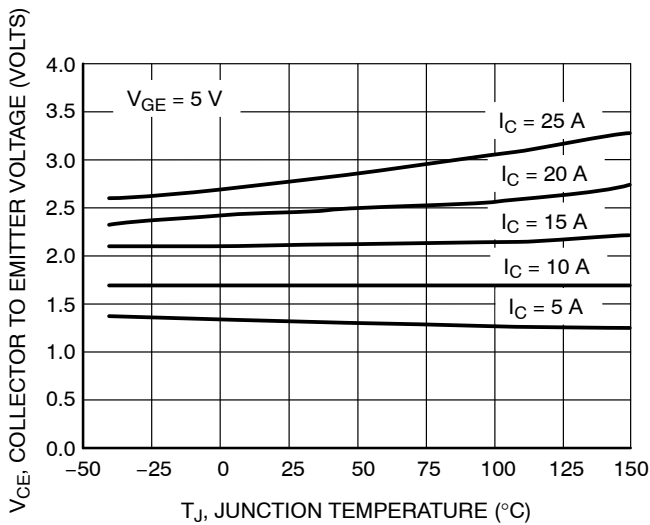
**Figure 2. Output Characteristics**



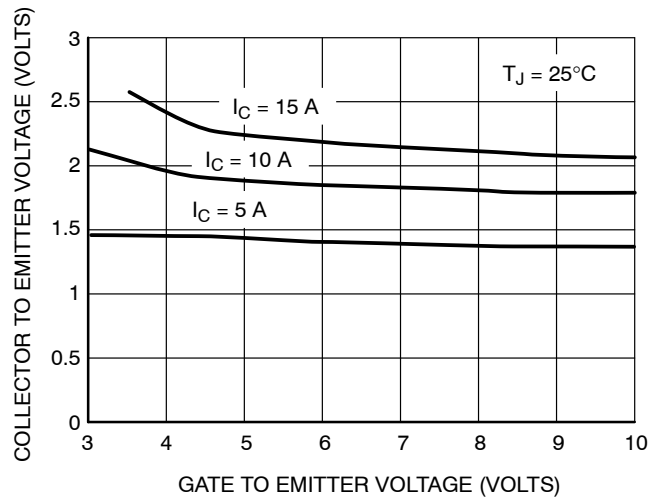
**Figure 3. Output Characteristics**



**Figure 4. Transfer Characteristics**



**Figure 5. Collector-to-Emitter Saturation Voltage versus Junction Temperature**



**Figure 6. Collector-to-Emitter Voltage versus Gate-to-Emitter Voltage**

NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL

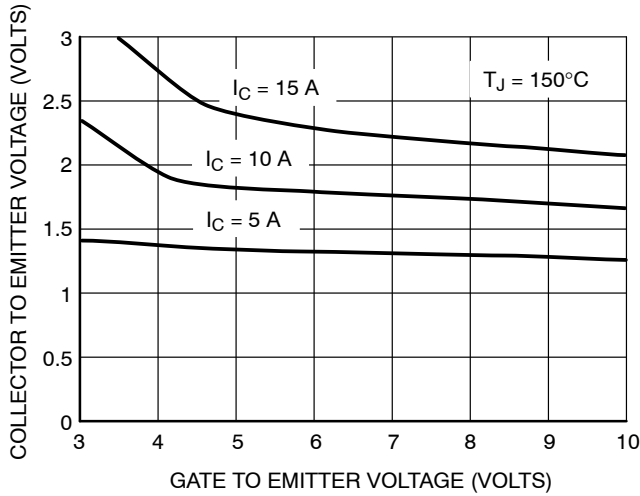


Figure 7. Collector-to-Emitter Voltage versus Gate-to-Emitter Voltage

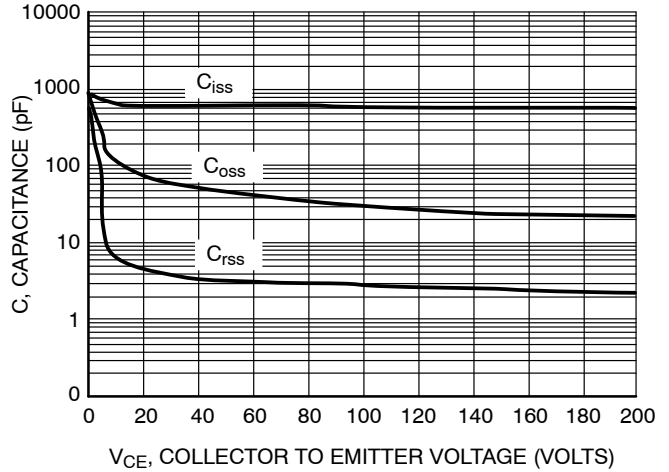


Figure 8. Capacitance Variation

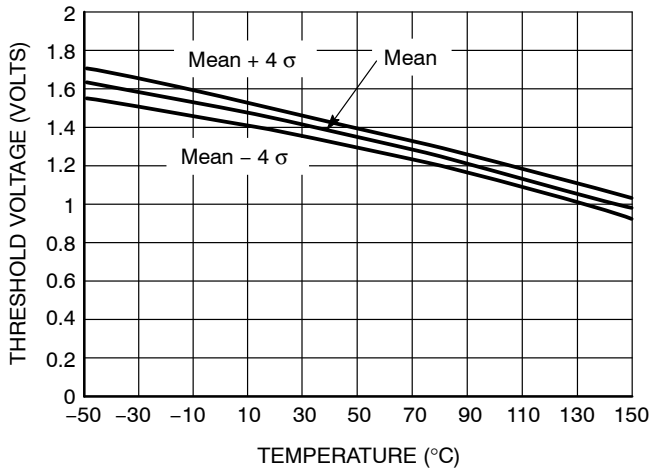


Figure 9. Gate Threshold Voltage versus Temperature

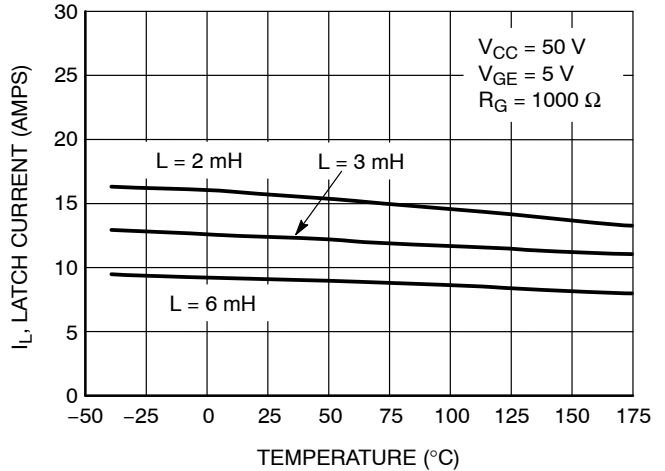


Figure 10. Minimum Open Secondary Latch Current versus Temperature

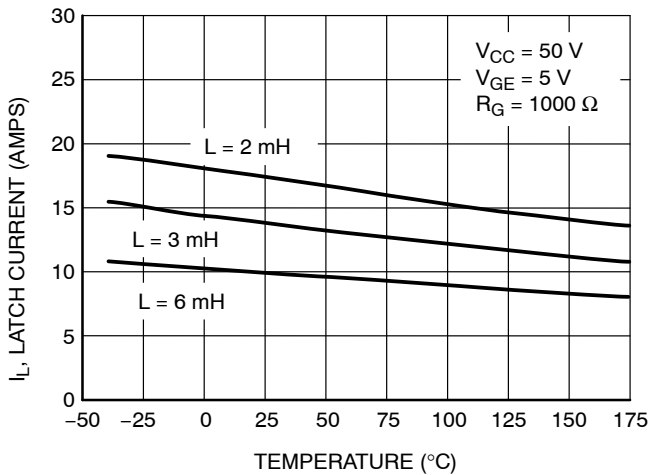


Figure 11. Typical Open Secondary Latch Current versus Temperature

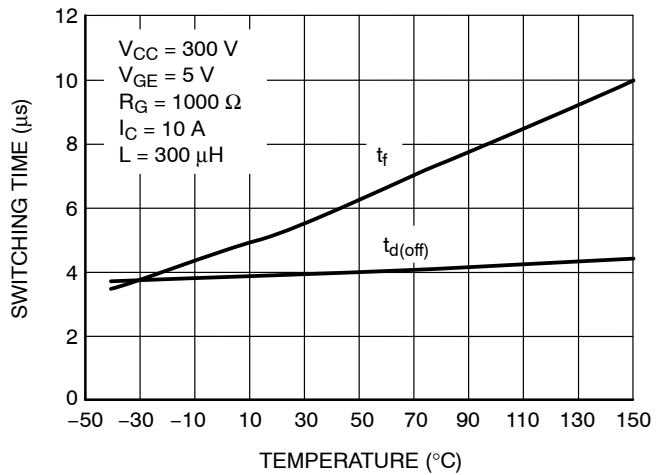
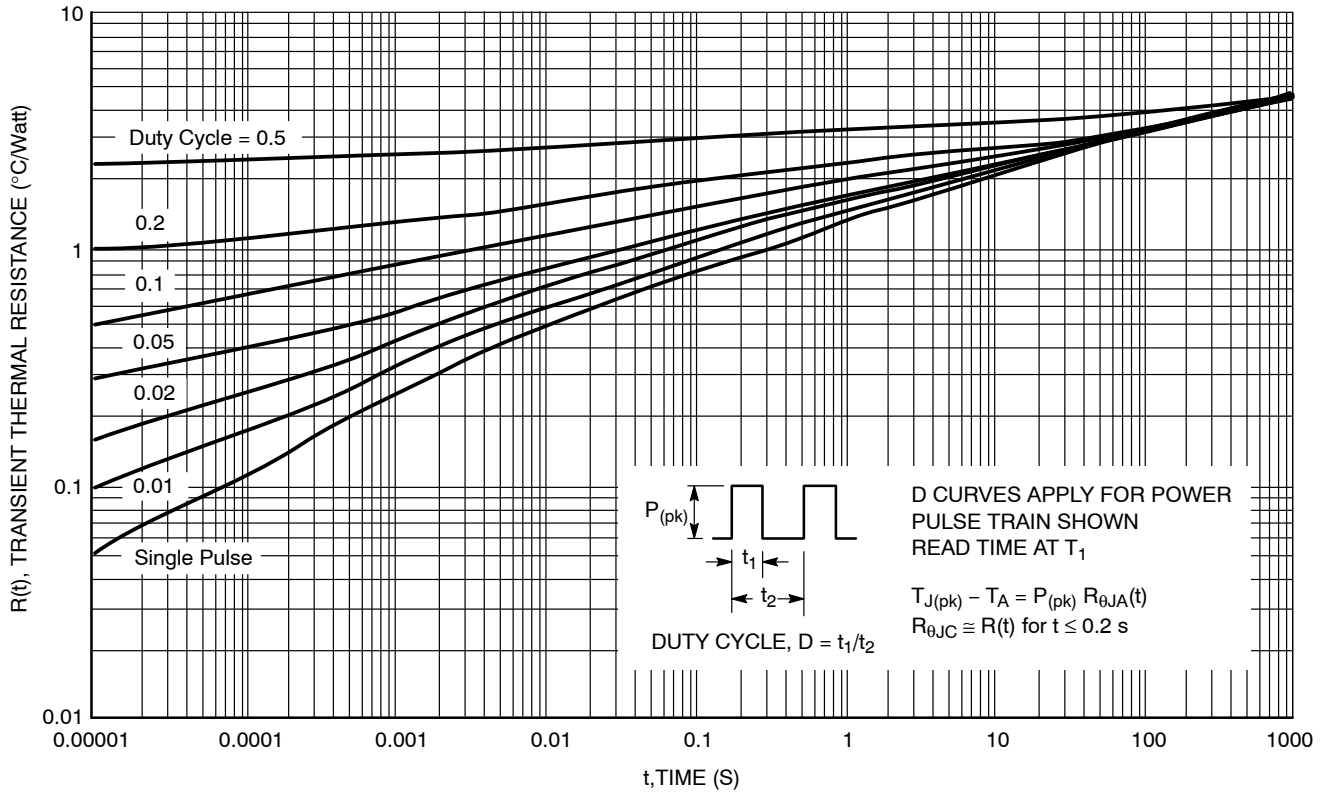
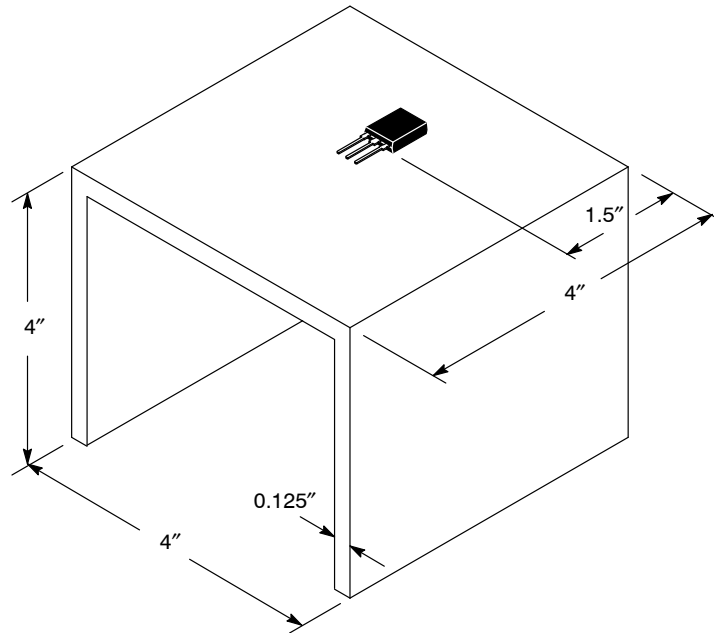


Figure 12. Inductive Switching Fall Time versus Temperature

NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL,  
NGP15N41ACL

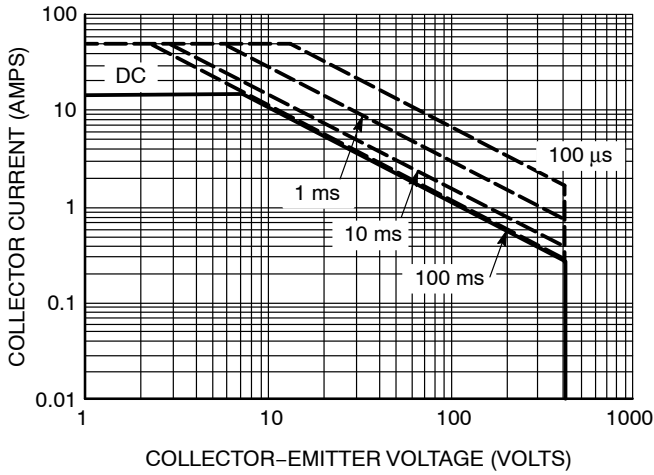


**Figure 13. Transient Thermal Resistance  
(Non-normalized Junction-to-Ambient mounted on  
fixture in Figure 14)**

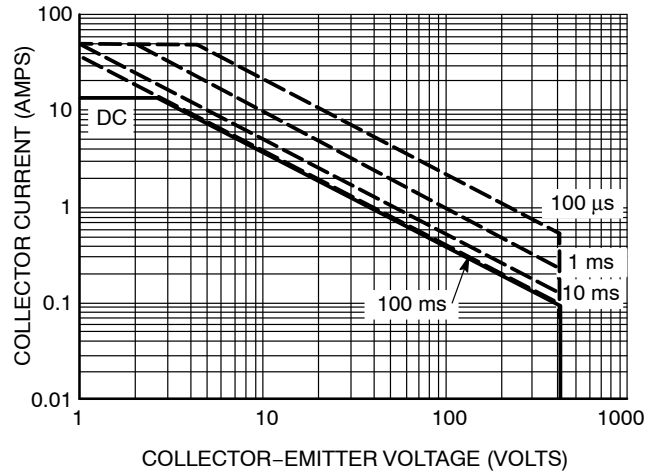


**Figure 14. Test Fixture for Transient Thermal Curve  
(48 square inches of 1/8" thick aluminum)**

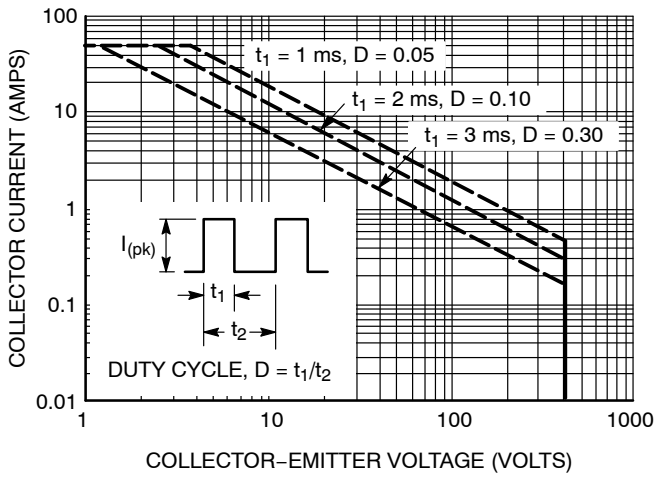
**NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL,  
NGP15N41ACL**



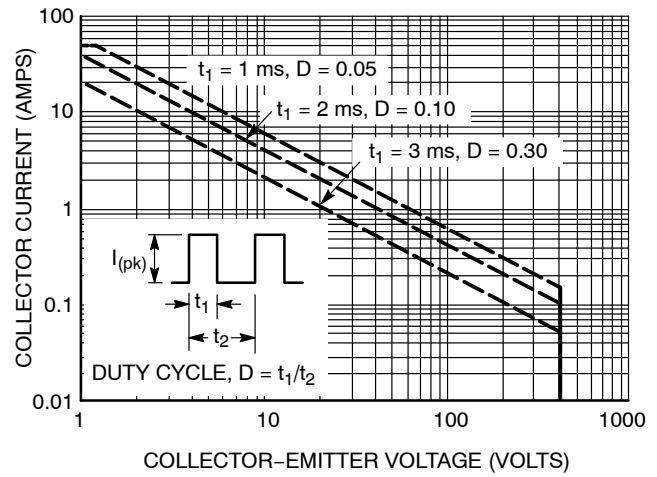
**Figure 15. Single Pulse Safe Operating Area  
(Mounted on an Infinite Heatsink at  $T_A = 25^\circ\text{C}$ )**



**Figure 16. Single Pulse Safe Operating Area  
(Mounted on an Infinite Heatsink at  $T_A = 125^\circ\text{C}$ )**



**Figure 17. Pulse Train Safe Operating Area  
(Mounted on an Infinite Heatsink at  $T_C = 25^\circ\text{C}$ )**



**Figure 18. Pulse Train Safe Operating Area  
(Mounted on an Infinite Heatsink at  $T_C = 125^\circ\text{C}$ )**

# NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL

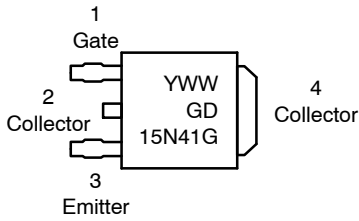
## ORDERING INFORMATION

Device	Package Type	Shipping†
NGD15N41CLT4G	DPAK (Pb-Free)	2500/Tape & Reel
NGD15N41ACL4G		
NGB15N41CLT4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel
NGB15N41ACL4G		
NGP15N41CLG	TO-220 (Pb-Free)	50 Units/Rail
NGP15N41ACLG		

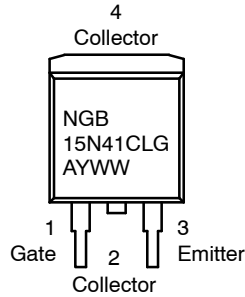
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## MARKING DIAGRAMS

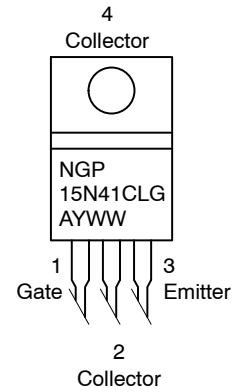
**DPAK  
CASE 369C  
STYLE 7**



**D<sup>2</sup>PAK  
CASE 418B  
STYLE 4**



**TO-220AB  
CASE 221A  
STYLE 9**



A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Device



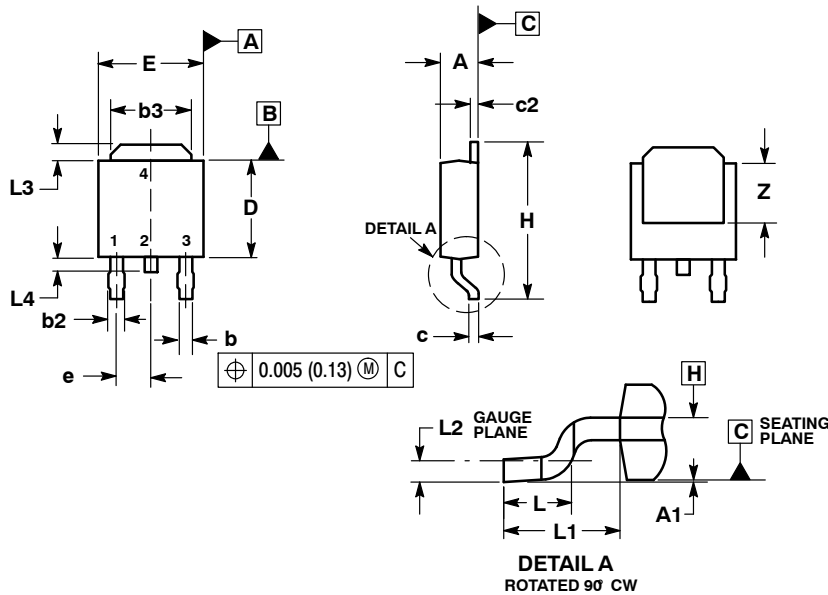
NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL,  
NGP15N41ACL

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)

CASE 369C-01

ISSUE D

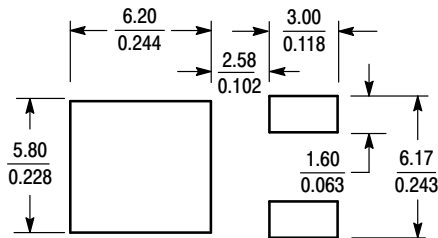


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT\*



SCALE 3:1 (mm / inches)

STYLE 2:

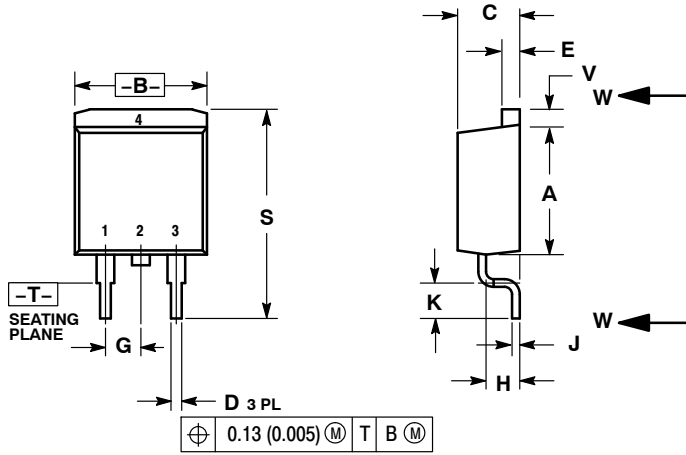
- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL,  
NGP15N41ACL

PACKAGE DIMENSIONS

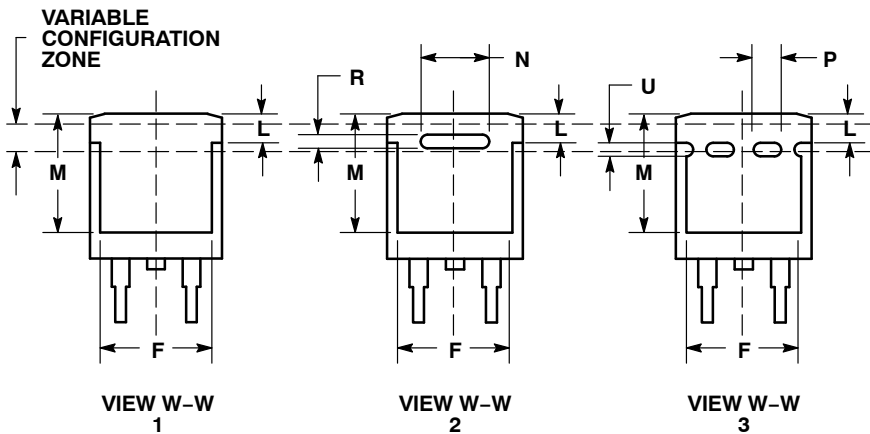
D<sup>2</sup>PAK  
CASE 418B-04  
ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

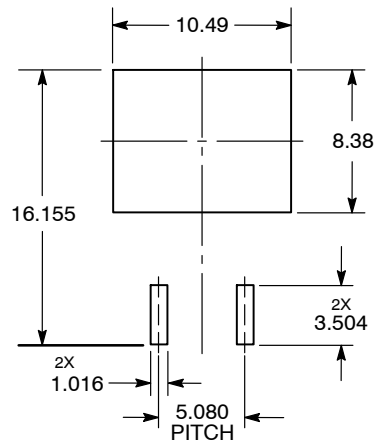
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



STYLE 4:

- PIN 1. GATE
- COLLECTOR
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT\*



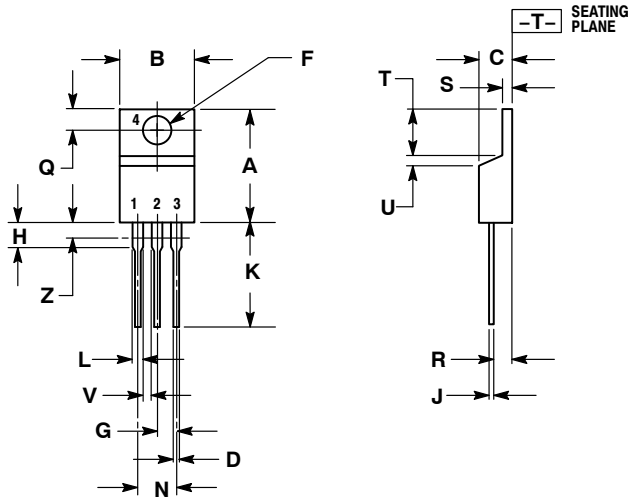
DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NGD15N41CL, NGD15N41ACL, NGB15N41CL, NGB15N41ACL, NGP15N41CL, NGP15N41ACL

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AF



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 9:

- PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

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